






-  100% EAS Guaranteed
-  Green Device Available
-  Super Low Gate Charge
-  Excellent CdV/dt effect decline
-  Advanced high cell density Trench technology

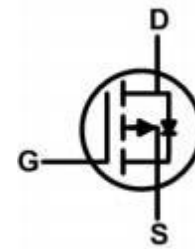

Product Summary

BVDSS	RDSON	ID
-40V	6.4mΩ	-80A

Description

The XXW80P04 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW80P04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration

Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	-80	A
	T _C =100°C		-50.6	
Pulsed Drain Current ¹		I _{DM}	-320	A
Single Pulse Avalanche Energy ²		EAS	101.25	mJ
Total Power Dissipation	T _C =25°C	P _D	81.16	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R _{θJA}	54	°C/W
Thermal Resistance from Junction-to-Case	R _{θJC}	1.54	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-40	-	-	V	
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -40V, V _{GS} = 0V	T _J =25°C	-	-	-1	pA
			T _J =100°C	-	-	-100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V	
Drain-Source on-Resistance ⁴	R _{DS(on)}	V _{GS} = -10V, I _D = -20A	-	6.4	8.2	mΩ	
		V _{GS} = -4.5V, I _D = -15A	-	8.2	11		
Forward Transconductance ⁴	g _{fs}	V _{DS} = -10V, I _D = -20A	-	104	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C _{iss}	V _{DS} = -20V, V _{GS} = 0V, f = 1MHz	-	5295	-	pF	
Output Capacitance	C _{oss}		-	430	-		
Reverse Transfer Capacitance	C _{rss}		-	385	-		
Gate Resistance	R _g	f = 1MHz	-	4.3	-	Q	
Switching Characteristics⁵							
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} = -20V, I _D = -20A	-	110	-	nC	
Gate-Source Charge	Q _{gs}		-	12.5	-		
Gate-Drain Charge	Q _{gd}		-	23	-		
Turn-on Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -20V, R _G = 3Ω, I _D = -20A	-	16.8	-	ns	
Rise Time	t _r		-	10	-		
Turn-off Delay Time	t _{d(off)}		-	65	-		
Fall Time	t _f		-	17	-		
Body Diode Reverse Recovery Time	t _{rr}	I _F = -20A, dI/dt = 100A/μs	-	42	-	ns	
Body Diode Reverse Recovery Charge	Q _{rr}		-	29	-	nC	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V _{SD}	I _S = -20A, V _{GS} = 0V	-	-	-1.2	V	
Continuous Source Current	I _S	T _C = 25°C	-	-	-80	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The EAS data shows Max. rating. The test condition is V_{DD} = -30V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -45A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

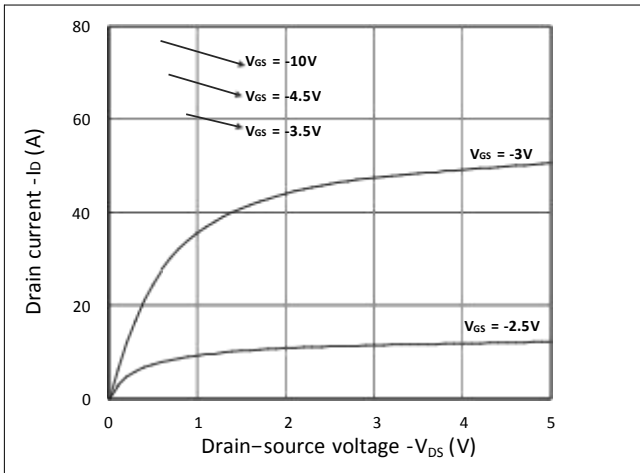


Figure 1. Output Characteristics

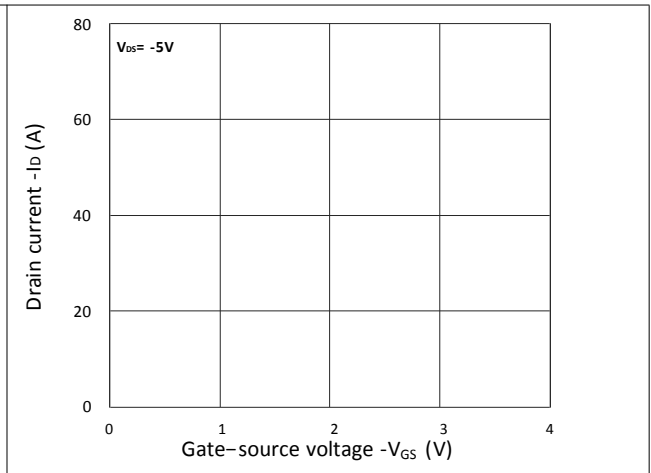


Figure 2. Transfer Characteristics

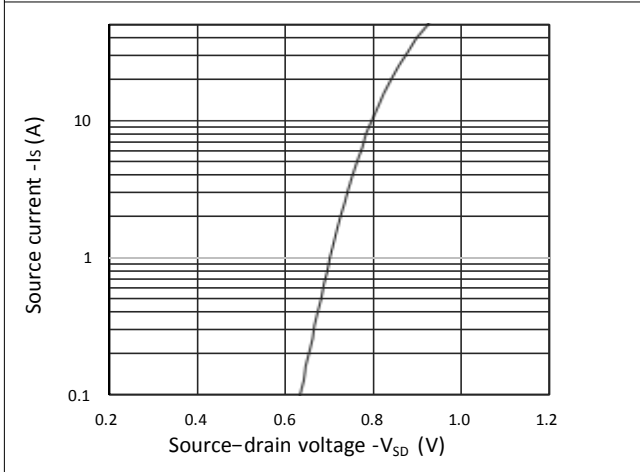


Figure 3. Forward Characteristics of Reverse

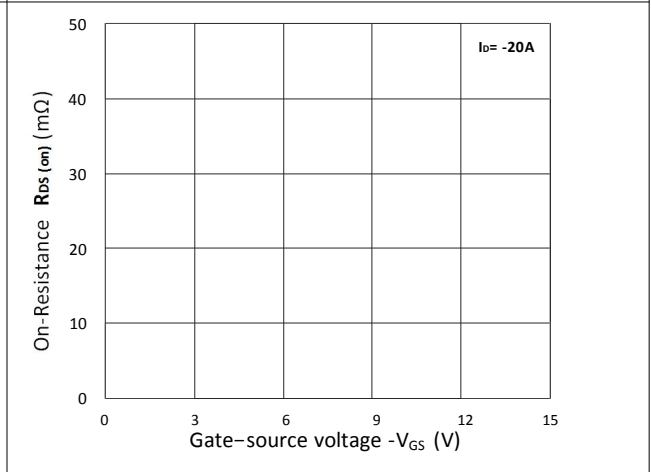


Figure 4. $R_{DS(ON)}$ vs V_{GS}

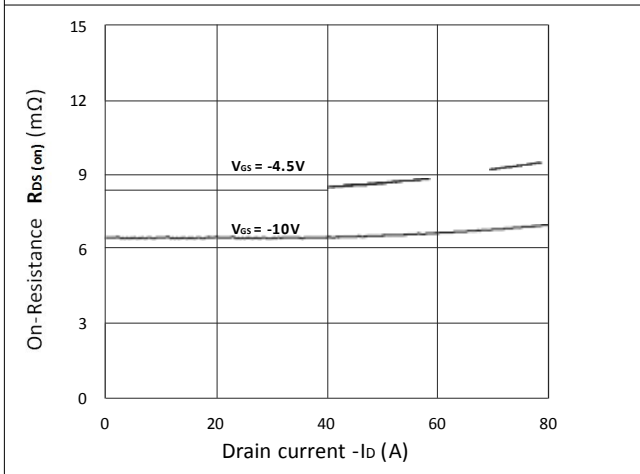


Figure 5. $R_{DS(ON)}$ vs I_D

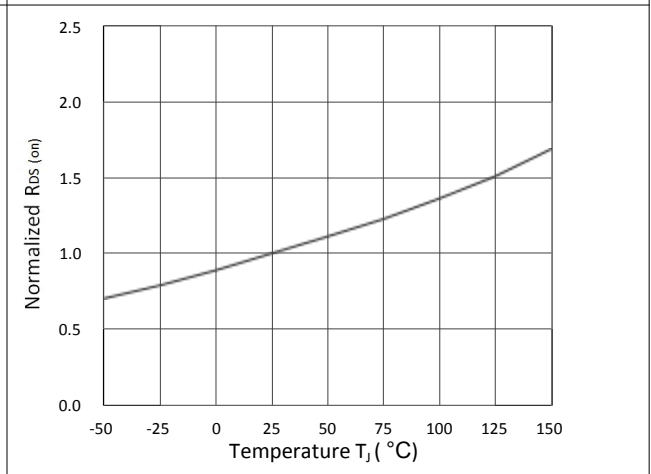


Figure 6. Normalized $R_{DS(ON)}$ vs Temperature

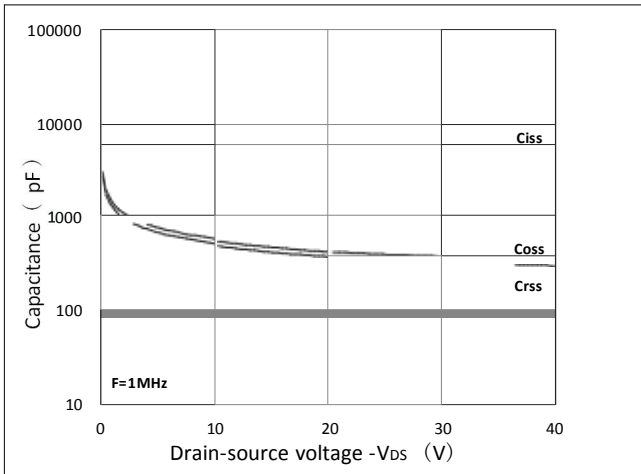


Figure 7. Capacitance Characteristics

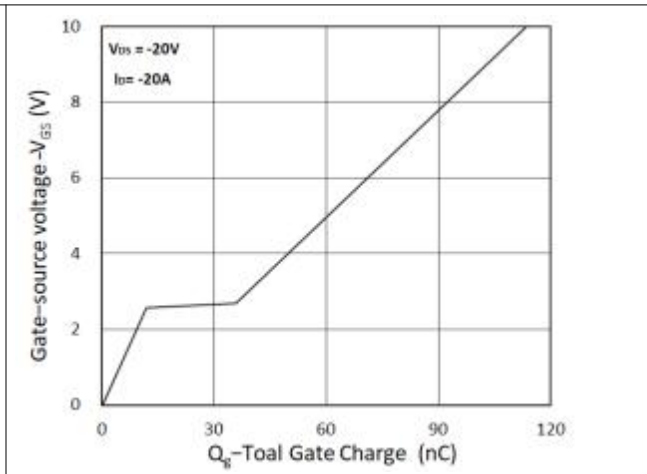


Figure 8. Gate Charge Characteristics

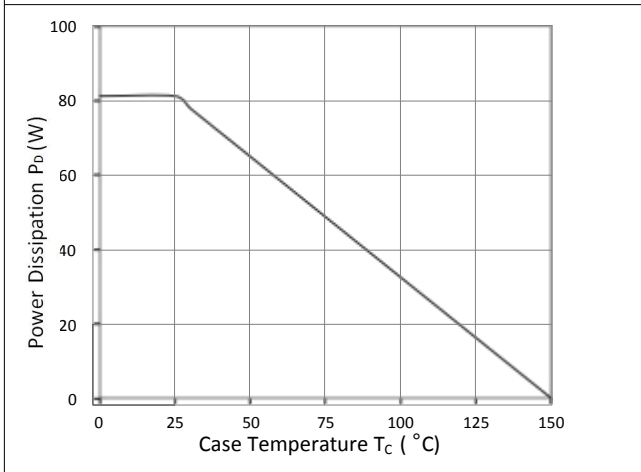


Figure 9. Power Dissipation

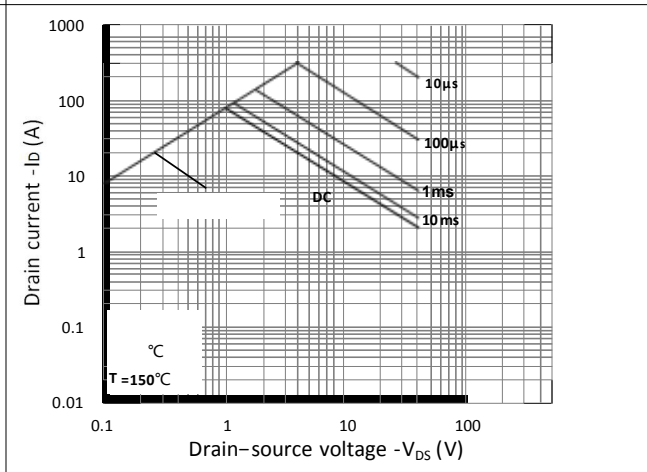


Figure 10. Safe Operating Area

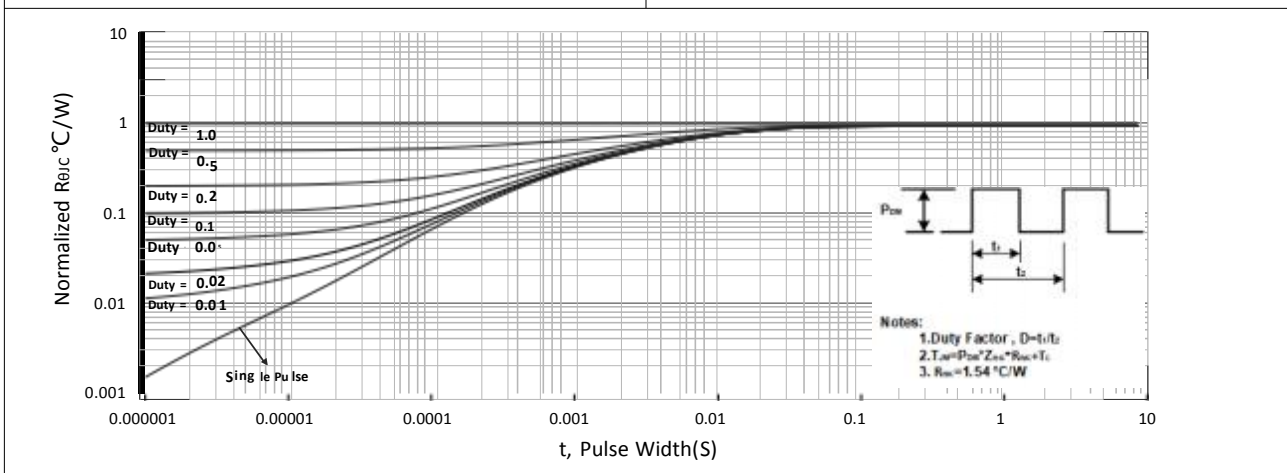


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

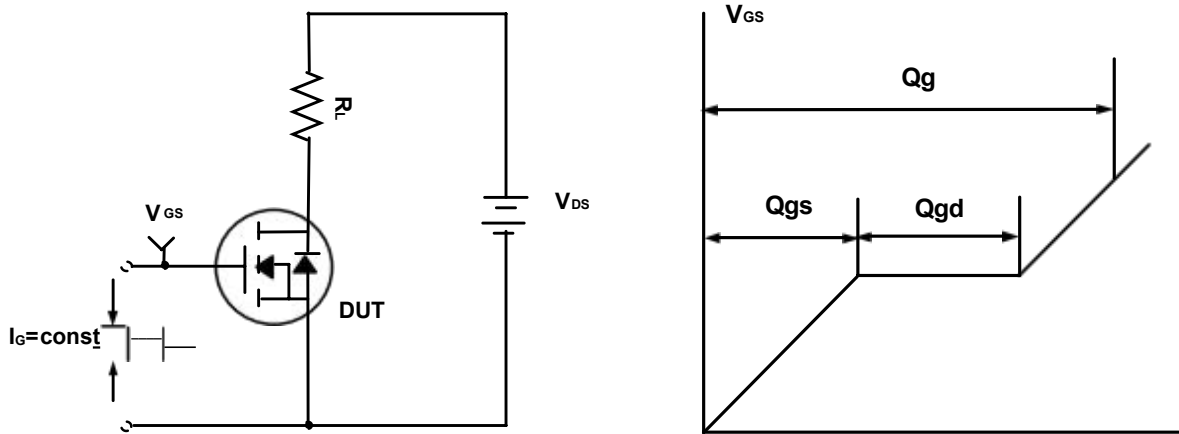


Figure A. Gate Charge Test Circuit & Waveforms

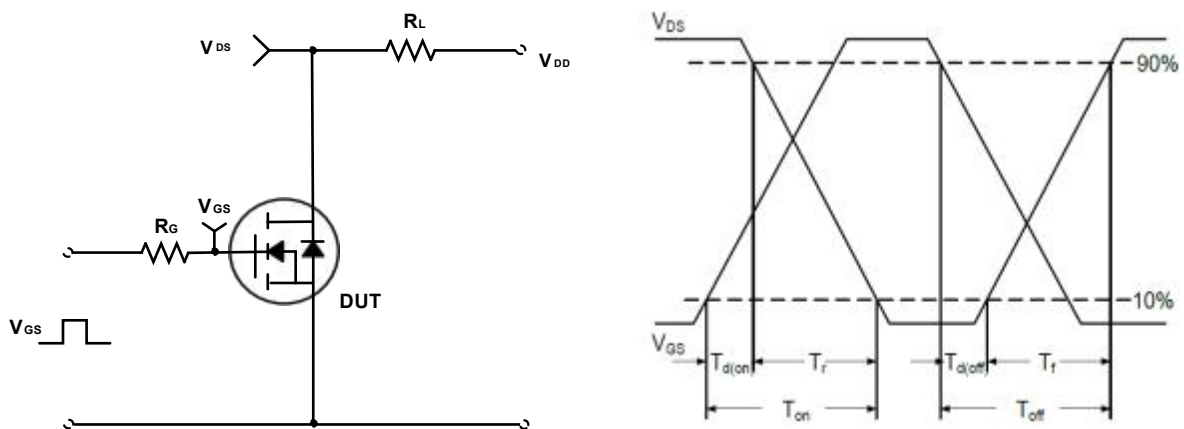


Figure B. Switching Test Circuit & Waveforms

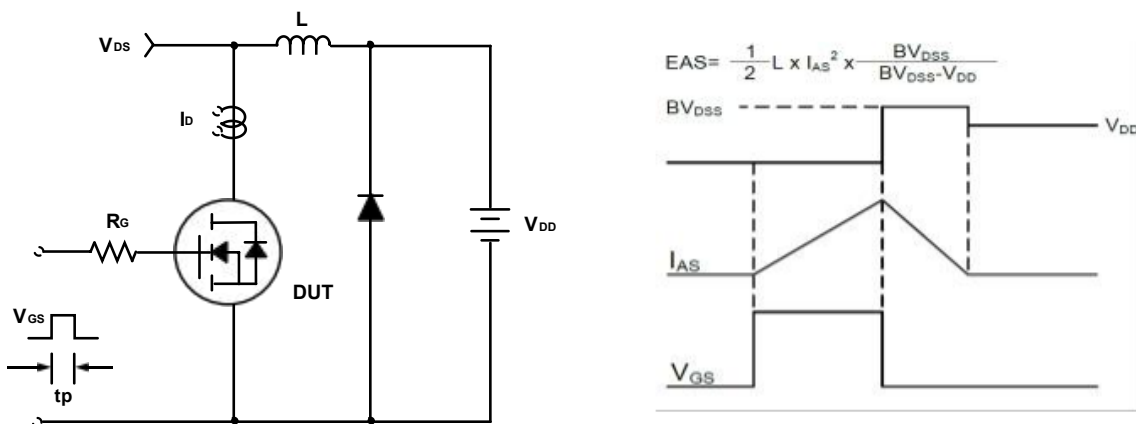
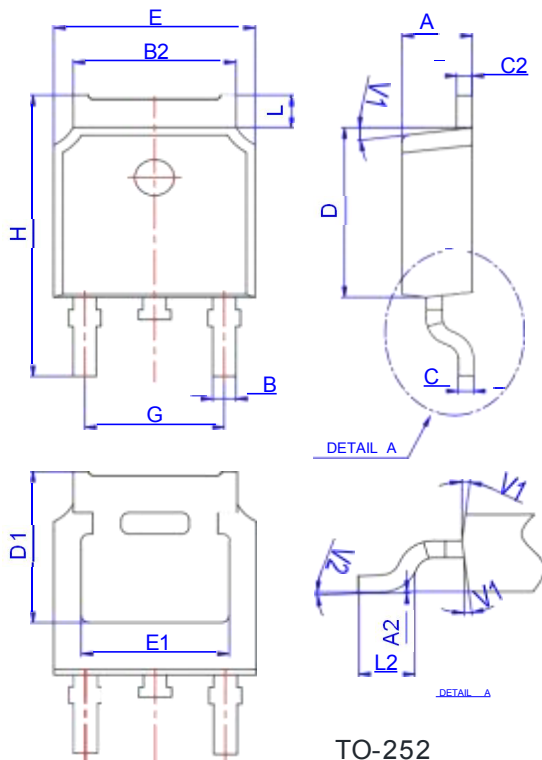
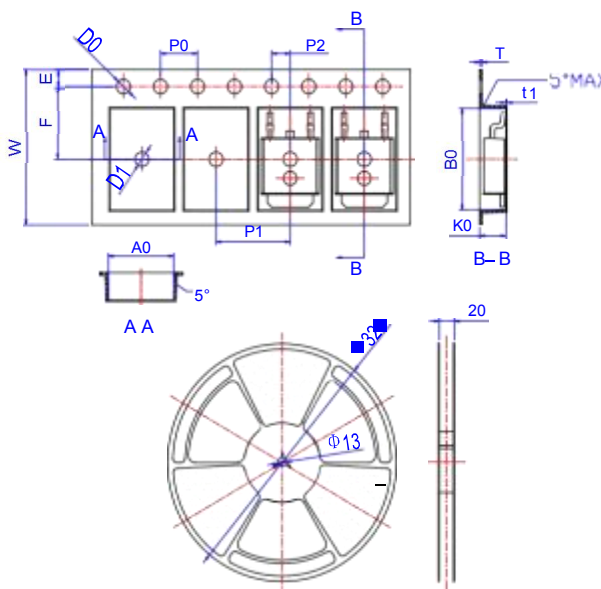


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Package Mechanical Data-TO-252


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Lead Specification-TO-252


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583